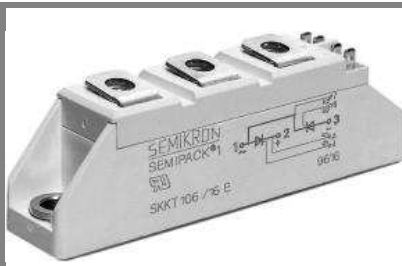


SKMT 92, SKKL 92



SEMIPACK® 1

Thyristor / Diode Modules

SKKL 92
SKMT 92

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

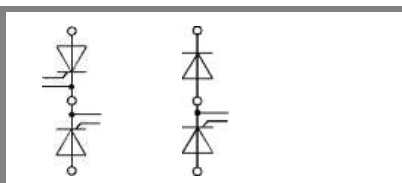
Typical Applications

- Line rectifiers for transistorized AC motor controllers (SKKL)
- DC braking of AC motor (SKMT)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	$I_{TRMS} = 150$ A (maximum value for continuous operation) $I_{TAV} = 95$ A (sin. 180; $T_c = 85$ °C)	
900	800	SKMT 92/08E	SKKL 92/12E
1300	1200		
1500	1400	SKMT 92/14E	
1700	1600	SKMT 92/16E	SKKL 92/16E
1900	1800	SKMT 92/18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; $T_c = 85$ (100) °C;	95 (68)	A
I_D	P3/180; $T_a = 45$ °C; B2 / B6 P3/180F; $T_a = 35$ °C; B2 / B6	70 / 85 140 / 175	A
I_{RMS}	P3/180F; $T_a = 35$ °C; W1 / W3	190 / 3 * 135	A
I_{TSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 125$ °C; 10 ms	2000 1750	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 125$ °C; 8,3 ... 10 ms	20000 15000	A ² s
V_T	$T_{vj} = 25$ °C; $I_T = 300$ A	max. 1,65	V
$V_{T(TO)}$	$T_{vj} = 125$ °C	max. 0,9	V
r_T	$T_{vj} = 125$ °C	max. 2	mΩ
I_{DD}, I_{RD}	$T_{vj} = 125$ °C; $V_{RD} = V_{RRM}; V_{DD} = V_{DRM}$	max. 20	mA
t_{gd}	$T_{vj} = 25$ °C; $I_G = 1$ A; $di_G/dt = 1$ A/μs	1	μs
t_{gr}	$V_D = 0,67 * V_{DRM}$	2	μs
$(di/dt)_{cr}$	$T_{vj} = 125$ °C	max. 150	A/μs
$(dv/dt)_{cr}$	$T_{vj} = 125$ °C	max. 1000	V/μs
t_q	$T_{vj} = 125$ °C	100	μs
I_H	$T_{vj} = 25$ °C; typ. / max.	150 / 250	mA
I_L	$T_{vj} = 25$ °C; $R_G = 33$ Ω; typ. / max.	300 / 600	mA
V_{GT}	$T_{vj} = 25$ °C; d.c.	min. 3	V
I_{GT}	$T_{vj} = 25$ °C; d.c.	min. 150	mA
V_{GD}	$T_{vj} = 125$ °C; d.c.	max. 0,25	V
I_{GD}	$T_{vj} = 125$ °C; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,28 / 0,14	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,3 / 0,15	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,32 / 0,16	K/W
$R_{th(c-s)}$	per thyristor / per module	0,2 / 0,1	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min. to heatsink	3600 / 3000 5 ± 15 % ¹⁾	V~ Nm
M_s	to terminals	3 ± 15 %	Nm
M_t		5 * 9,81	m/s ²
a		95	g
m	approx.		
Case	SKMT SKKL	A 72 A 59	



SKMT

SKKL

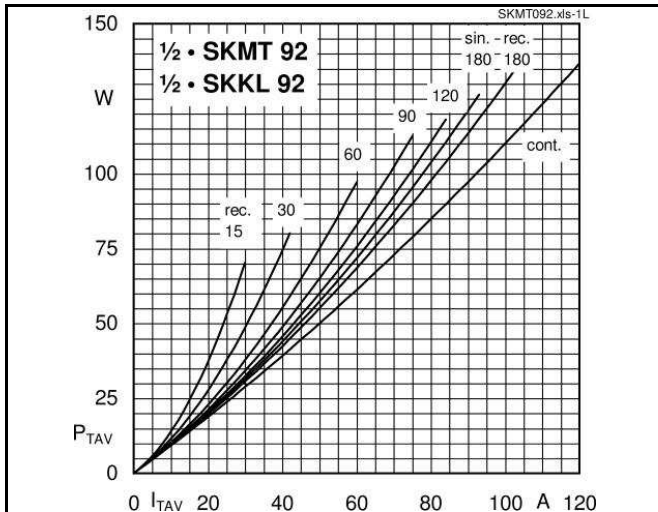


Fig. 1L Power dissipation per thyristor vs. on-state current

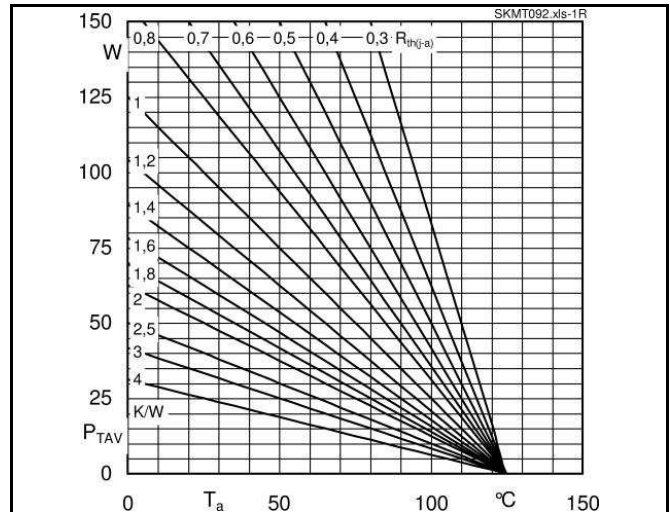


Fig. 1R Power dissipation per thyristor vs. ambient temp.

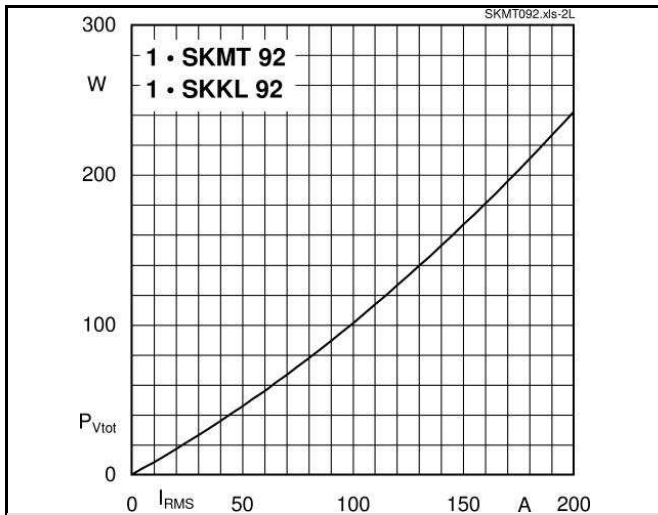


Fig. 2L Power dissipation per module vs. rms current

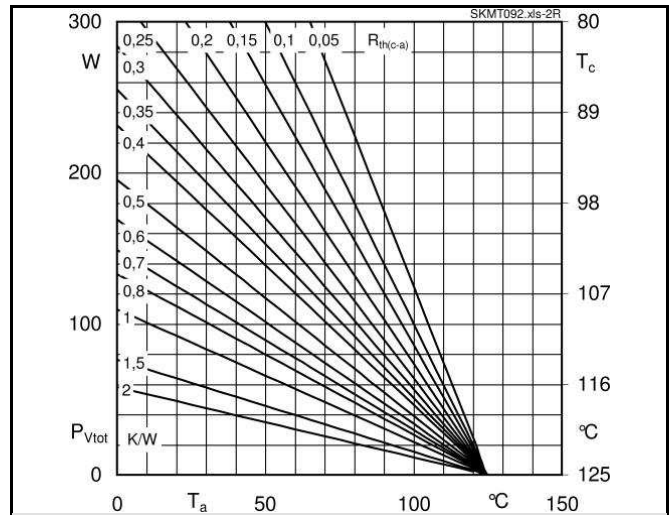


Fig. 2R Power dissipation per module vs. case temp.

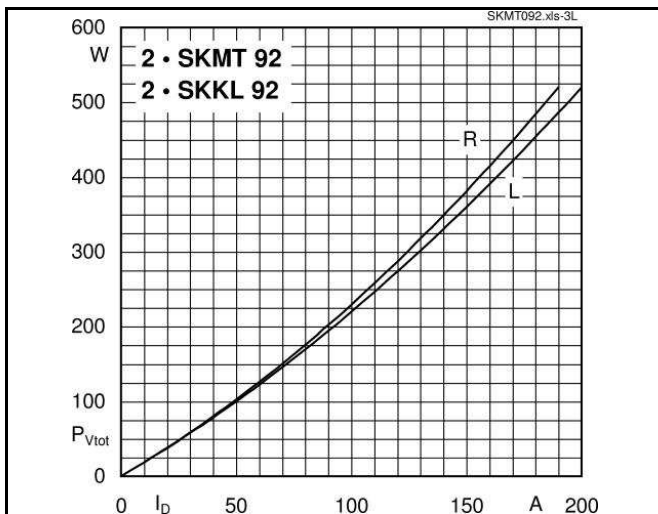


Fig. 3L Power dissipation of two modules vs. direct current

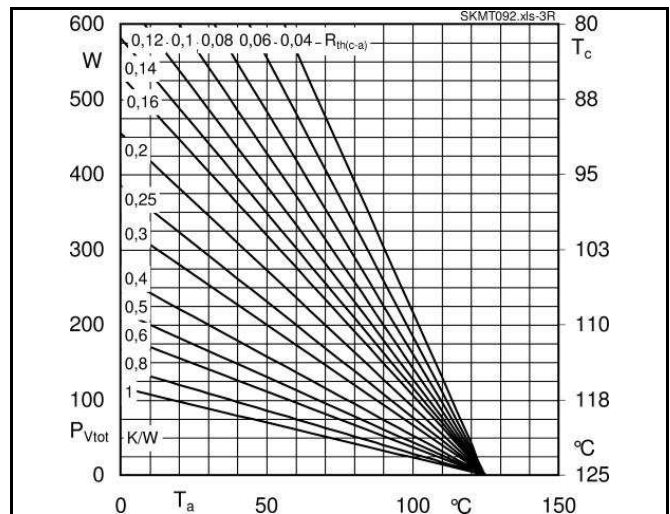


Fig. 3R Power dissipation of two modules vs. case temp.

SKMT 92, SKKL 92

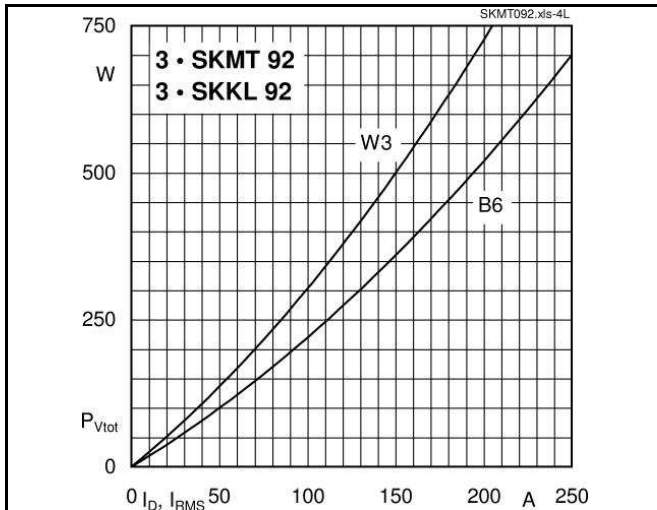


Fig. 4L Power dissipation of three modules vs. direct and rms current

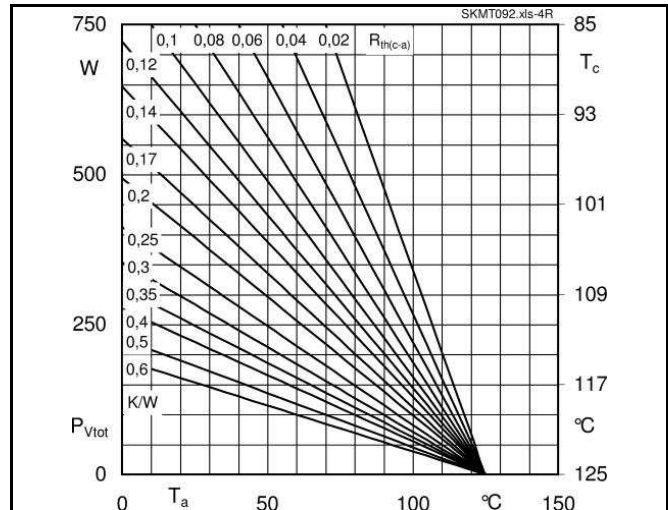


Fig. 4R Power dissipation of three modules vs. case temp.

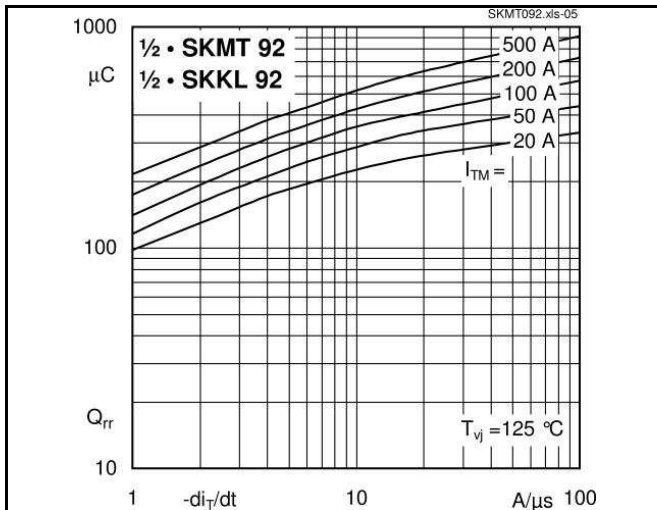


Fig. 5 Recovered charge vs. current decrease

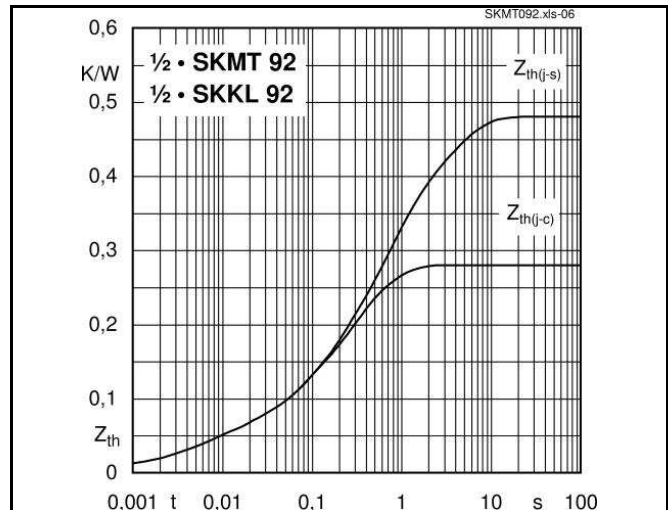


Fig. 6 Transient thermal impedance vs. time

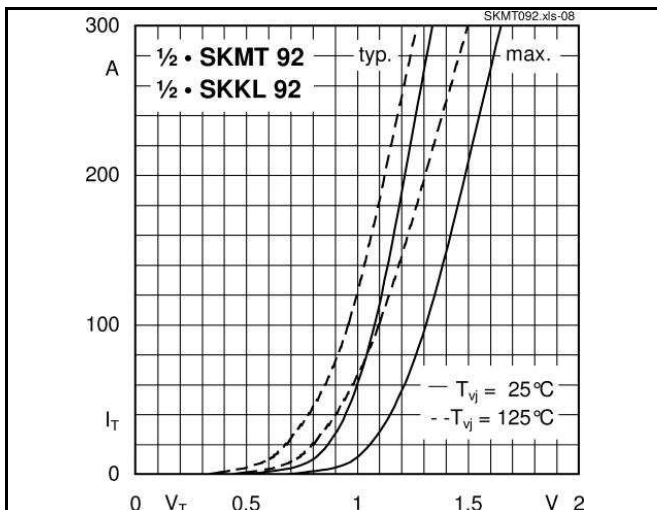


Fig. 7 On-state characteristics

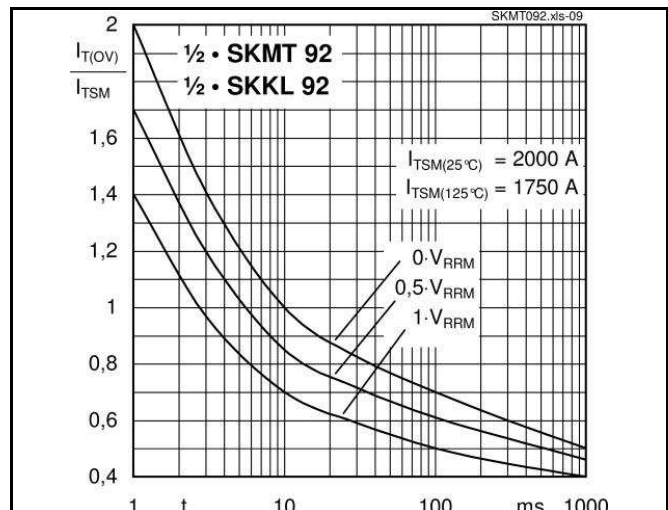
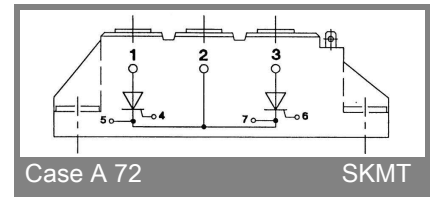
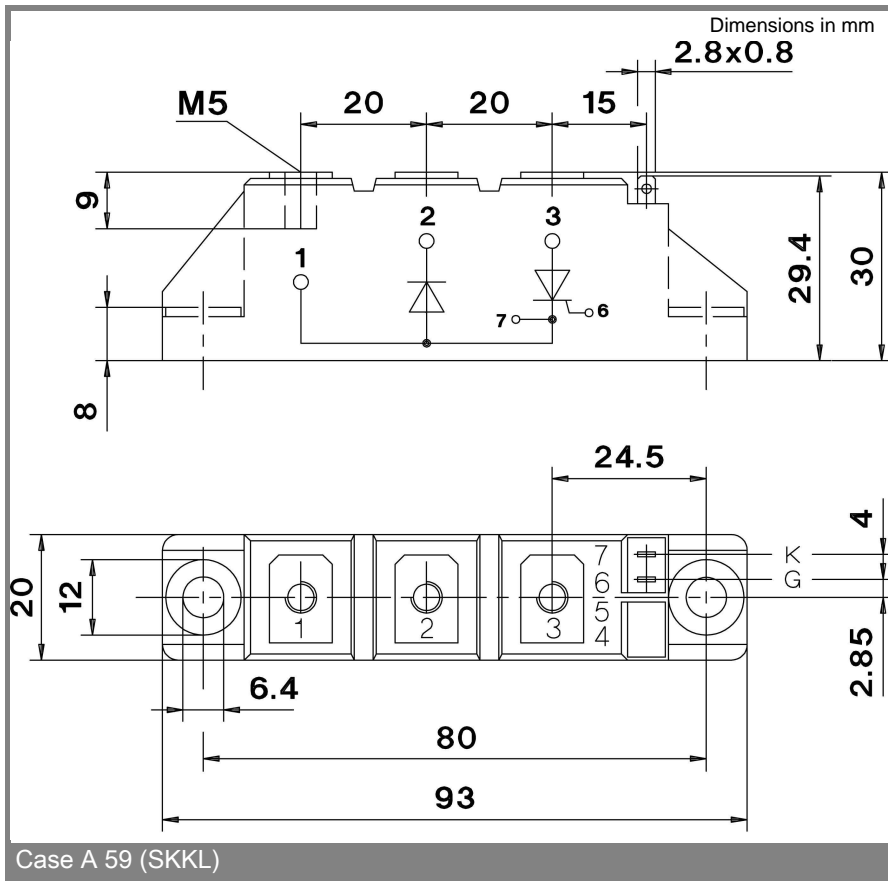
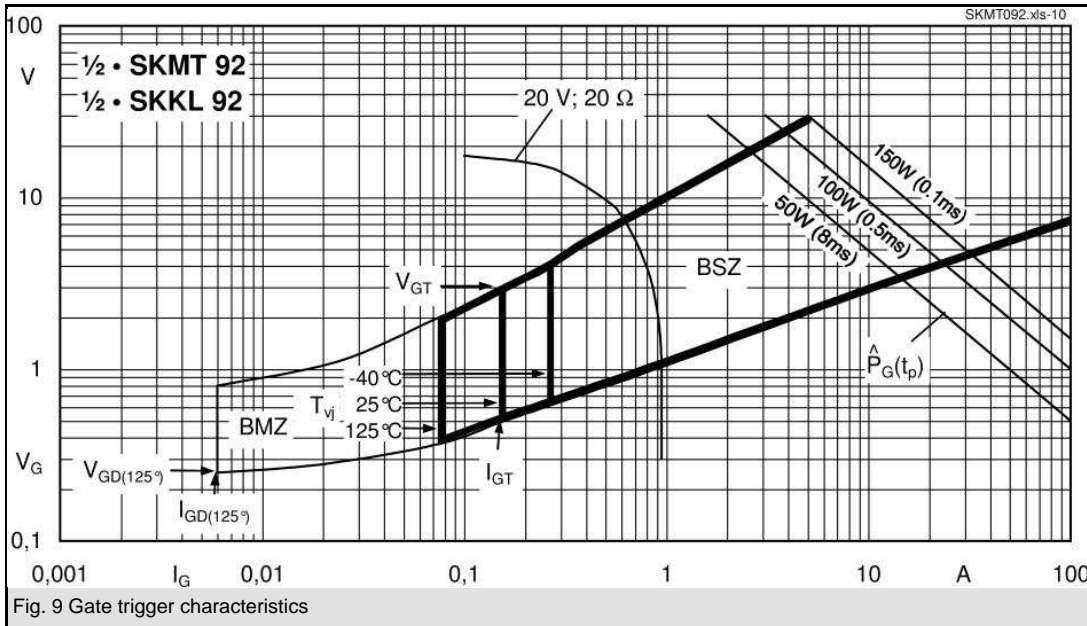


Fig. 8 Surge overload current vs. time



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